

ABSTRACT OF THE DISCLOSURE

The semiconductor device comprises a capacitor including a storage electrode 76, a capacitor dielectric film formed on the storage electrode 76, and a plate electrode formed on the capacitor dielectric film 78, the storage electrode 76 having an upper end rounded and having a larger thickness at the upper end than a thickness in the rest region. Whereby electric field concentration on the upper end of the storage electrode can be mitigated, and leakage current increase and dielectric breakdown of the capacitor dielectric film can be precluded.